Docket No.: P2001,0373

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : JUDITH MAGET

Filed : CONCURRENTLY HEREWITH

Title : INTEGRATED, TUNABLE CAPACITANCE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

S i r :

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent No. 6,172,378 B1 (Hull et al.), dated January 9, 2001;

U.S. Patent No. 5,965,912 (Stolfa et al.), dated October 12, 1999;

U.S. Patent No. 6,034,388 (Brown et al.), dated March 7, 2000;

Patent Abstracts of Japan 03147376 A (Hidetomo), dated June 24, 1991;

European Patent Application EP 0 800 218 A2 (McFarland et al.), dated October 8, 1997;

Hung, C.-M. et al.: "A 25.9-GHz Voltage-Controlled Oscillator Fabricated in a CMOS Process", Symposium on VLSI Circuits Digest of Technical Papers, IEEE, 2000, pp. 100-101;

Maget, J. et al.: "A Varactor with High Capacitance Tuning Range in Standard 0.25µm CMOS Technology", 4 pages;

Burghartz, J. N. et al.: "Integrated RF and Microwave Components in BiCMOS Technology", IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1559-1570;

Wong, W. M. Y. et al.: "A Wide Tuning Range Gated Varactor", IEEE Journal of Solid-State Circuits, Vol. 35, No. 5, May 2000, pp. 773-779;

Svelto, F. et al.: "A Three Terminal Varactor for RF IC's in Standard CMOS Technology", IEEE Transactions on Electron Devices, Vol. 47, No. 4, April 2000, pp. 893-895;

Tiebout, M.: "A Fully Integrated 1.3GHz VCO for GSM in 0.25µm Standard CMOS with a Phasenoise of –142dBc/Hz at 3MHz Offset", European Microwave Week, 2000, 4 pages;

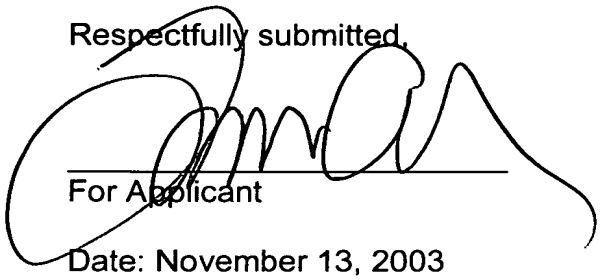
Andreani, P. et al.: "On the Use of MOS Varactors in RF VCO's", IEEE Journal of Solid-State Circuits, Vol. 35, No. 6, June 2000, pp. 905-910;

Porret, A.-S. et al.: "Design of High-Q Varactors for Low-Power Wireless Applications Using a Standard CMOS Process", IEEE Journal of Solid-State Circuits, Vol. 35, No. 3, March 2000, pp. 337-345;

International Search Report, dated December 4, 2002.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant. As per the Notice in 1273 OG 55 (August 5, 2003) no copies of any above-mentioned U.S. patents and U.S. patent application publications are submitted for any application filed after June 30, 2003.

Respectfully submitted,



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For Applicant

Date: November 13, 2003

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FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))	Attorney Docket No.: P2001,0373 Appl. No.: Applicant: JUDITH MAGET Filing Date: November 13, 2003 Group Art Unit:

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	6,172,378 B1	1/9/01	Hull et al.			
	B	5,965,912	10/12/99	Stolfa et al.			
	C	6,034,388	3/7/00	Brown et al.			
	D						
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FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	TRANSL. NO
	J	03147376 A	6/24/91	Japan				
	K	0 800 218	10/8/97	Europe				
	L							
	M							
	N							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

		Hung, C.-M. et al.: "A 25.9-GHz Voltage-Controlled Oscillator Fabricated in a CMOS Process", Symposium on VLSI Circuits Digest of Technical Papers, IEEE, 2000, pp. 100-101
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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